

VERSION WITH MARKINGS TO SHOW CHANGES MADE**In the Specification:**

The paragraph beginning at line 1 of page 9, as been amended as follows:

Formation of nanometer crystals of Group III-V semiconductors is described in copending and commonly assigned Alivisatos et al. U.S. Patent 5,751,018; Alivisatos et al. U.S. Patent 5,505,928; ~~Serial No. 08/235,265, filed April 29, 1994 as an FWC application of Serial No. 07/796,246, filed November 11, 1991;~~ and Alivisatos et al. U.S. Patent 5,262,357, which also describes the formation of Group II-VI semiconductor nanocrystals, and which is also assigned to the assignee of this invention. Also described therein is the control of the size of the semiconductor nanocrystals during formation using crystal growth terminators. The teachings of Alivisatos et al. U.S. Patent 5,751,018 ~~Serial No. 08/235,265~~, and Alivisatos et al. U.S. Patent 5,262,357 are each hereby specifically incorporated by reference.

09865130-05401
F04250-0E759860